

FEATURES

44 V supply maximum ratings

V_{SS} to V_{DD} analog signal range

Low on resistance (45 Ω max)

Low ΔR_{ON} (5 Ω max)

Low R_{ON} match (4 Ω max)

Low power dissipation

Fast switching times

$t_{ON} < 175$ ns

$t_{OFF} < 145$ ns

Low leakage currents (5 nA max)

Low charge injection (10 pC max)

Break-before-make switching action

APPLICATIONS

Audio and video switching

Battery-powered systems

Test equipment

Communication systems

GENERAL DESCRIPTION

The ADG333A is a monolithic CMOS device comprising four independently selectable SPDT switches. It is designed on an LC²MOS process, which provides low power dissipation yet achieves a high switching speed and a low on resistance.

The on resistance profile is very flat over the full analog input range, ensuring good linearity and low distortion when switching audio signals. High switching speed also makes the part suitable for video signal switching. CMOS construction ensures ultralow power dissipation, making the part ideally suited for portable, battery-powered instruments.

When they are on, each switch conducts equally well in both directions and has an input signal range that extends to the power supplies. In the off condition, signal levels up to the supplies are blocked. All switches exhibit break-before-make switching action for use in multiplexer applications. Inherent in the design is low charge inject

FUNCTIONAL BLOCK DIAGRAM

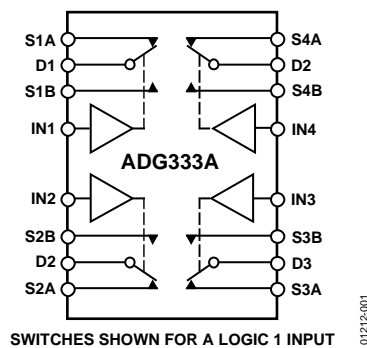


Figure 1.

PRODUCT HIGHLIGHTS

1. Extended signal range.
The ADG333A is fabricated on an enhanced LC²MOS process, giving an increased signal range which extends to the supply rails.
2. Low power dissipation.
3. Low R_{ON} .
4. Single-supply operation.
For applications where the analog signal is unipolar, the ADG333A can be operated from a single rail power supply. The part is fully specified with a single 12 V supply.

Rev. A

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REVISION HISTORY

3/05—Rev. 0 to Rev. A	
Updated Format.....	Universal
Changes to Specifications Tables.....	3
Updated Outline Dimensions	12
Changes to Ordering Guide	12

10/95—Revision 0: Initial Version

SPECIFICATIONS

DUAL SUPPLY

$V_{DD} = +15\text{ V}$, $V_{SS} = -15\text{ V}$, GND = 0 V, unless otherwise noted.¹

Table 1.

Parameter	+25°C	−40°C to +85°C	Unit	Test Conditions/Comments
ANALOG SWITCH				
Analog Signal Range		V_{SS} to V_{DD}	V	
R_{ON}	20		Ω typ	$V_D = \pm 10\text{ V}$, $I_S = -1\text{ mA}$
	45	45	Ω max	
ΔR_{ON}		5	Ω max	$V_D = \pm 5\text{ V}$, $I_S = -10\text{ mA}$
R_{ON} Match		4	Ω max	$V_D = \pm 10\text{ V}$, $I_S = -10\text{ mA}$
LEAKAGE CURRENTS				
Source OFF Leakage I_S (OFF)	± 0.1		nA typ	$V_{DD} = +16.5\text{ V}$, $V_{SS} = -16.5\text{ V}$
	± 0.25	± 3	nA max	$V_D = \pm 15.5\text{ V}$, $V_S = +15.5\text{ V}$
Channel ON Leakage I_D , I_S (ON)	± 0.1		nA typ	Figure 15
	± 0.4	± 5	nA max	$V_S = V_D = \pm 15.5\text{ V}$
				Figure 16
DIGITAL INPUTS				
Input High Voltage, V_{INH}		2.4	V min	
Input Low Voltage, V_{INL}		0.8	V max	
Input Current				
I_{INL} or I_{INH}		± 0.005	μA typ	$V_{IN} = 0\text{ V}$ or V_{DD}
		± 0.5	μA max	
DYNAMIC CHARACTERISTICS²				
t_{ON}	90		ns typ	$R_L = 300\ \Omega$, $C_L = 35\text{ pF}$;
		175	ns max	$V_S = \pm 10\text{ V}$; Figure 17
t_{OFF}	80		ns typ	$R_L = 300\ \Omega$, $C_L = 35\text{ pF}$;
		145	ns max	$V_S = \pm 10\text{ V}$; Figure 17
Break-Before-Make Delay, t_{OPEN}	10		ns min	$R_L = 300\ \Omega$, $C_L = 35\text{ pF}$;
				$V_S = +5\text{ V}$; Figure 18
Charge Injection	2		pC typ	$V_D = 0\text{ V}$, $R_D = 0\ \Omega$, $C_L = 10\text{ nF}$;
	10		pC max	$V_{DD} = +15\text{ V}$, $V_{SS} = -15\text{ V}$; Figure 19
OFF Isolation	72		dB typ	$R_L = 75\ \Omega$, $C_L = 5\text{ pF}$, $f = 1\text{ MHz}$;
				$V_S = 2.3\text{ V rms}$; Figure 20
Channel-to-Channel Crosstalk	85		dB typ	$R_L = 75\ \Omega$, $C_L = 5\text{ pF}$, $f = 1\text{ MHz}$;
				$V_S = 2.3\text{ V rms}$; Figure 21
C_S (OFF)	7		pF typ	
C_D , C_S (ON)	26		pF typ	
POWER REQUIREMENTS				
I_{DD}	0.05		mA typ	Digital inputs = 0 V or 5 V
	0.25	0.35	mA max	
I_{SS}	0.01		μA typ	
	1	5	μA max	
V_{DD}/V_{SS}		$\pm 3/\pm 20$	V min/V max	$ V_{DD} = V_{SS} $

¹ Temperature range is as follows: B version: −40°C to +85°C.

² Guaranteed by design; not subject to production test.

ADG333A

SINGLE SUPPLY

$V_{DD} = +12\text{ V}$, $V_{SS} = 0\text{ V} \pm 10\%$, $GND = 0\text{ V}$, unless otherwise noted.¹

Table 2.

Parameter	+25°C	–40°C to +85°C	Unit	Test Conditions/Comments
ANALOG SWITCH				
Analog Signal Range		0 V to V_{DD}	V	
R_{ON}	35	75	Ω typ Ω max	$V_D = 1\text{ V}$, 10 V, $I_S = -1\text{ mA}$
LEAKAGE CURRENTS				$V_{DD} = 13.2\text{ V}$
Source OFF Leakage I_S (OFF)	± 0.1 ± 0.25	± 3	nA typ nA max	$V_D = 12.2\text{ V}/1\text{ V}$, $V_S = 1\text{ V}/12.2\text{ V}$ Figure 15
Channel ON Leakage I_D , I_S (ON)	± 0.1 ± 0.4	± 5	nA typ nA max	$V_S = V_D = 12.2\text{ V}/1\text{ V}$ Figure 16
DIGITAL INPUTS				
Input High Voltage, V_{INH}		2.4	V min	
Input Low Voltage, V_{INL}		0.8	V max	
Input Current I_{INL} or I_{INH}		± 0.005 ± 0.5	μA typ μA max	$V_{IN} = 0\text{ V}$ or V_{DD}
DYNAMIC CHARACTERISTICS ²				
t_{ON}	110	200	ns typ ns max	$R_L = 300\ \Omega$, $C_L = 35\text{ pF}$; $V_S = 8\text{ V}$; Figure 17
t_{OFF}	100	180	ns typ ns max	$R_L = 300\ \Omega$, $C_L = 35\text{ pF}$; $V_S = 8\text{ V}$; Figure 17
Break-Before-Make Delay, t_{OPEN}	10		ns min ns min	$R_L = 300\ \Omega$, $C_L = 35\text{ pF}$; $V_S = 5\text{ V}$; Figure 18
Charge Injection	5		pC typ	$V_D = 6\text{ V}$, $R_D = 0\text{ W}$, $C_L = 10\text{ nF}$; $V_{DD} = 12\text{ V}$, $V_{SS} = 0\text{ V}$; Figure 19
OFF Isolation	72		dB typ	$R_L = 75\ \Omega$, $C_L = 5\text{ pF}$, $f = 1\text{ MHz}$; $V_S = 1.15\text{ V rms}$; Figure 20
Channel-to-Channel Crosstalk	85		dB typ	$R_L = 75\ \Omega$, $C_L = 5\text{ pF}$, $f = 1\text{ MHz}$; $V_S = 1.15\text{ V rms}$; Figure 21
C_S (OFF)	12		pF typ	
C_D , C_S (ON)	25		pF typ	
POWER REQUIREMENTS				$V_{DD} = 13.5\text{ V}$
I_{DD}	0.05 0.25	0.35	mA typ mA max	Digital inputs = 0 V or 5 V
V_{DD}		$\pm 3/\pm 30$	V min/V max	

¹ Temperature range is as follows: B Version: –40°C to +85°C.

² Guaranteed by design; not subject to production test.

ABSOLUTE MAXIMUM RATINGS

$T_A = 25^\circ\text{C}$ unless otherwise noted.

Table 3.

Parameter	Min
V_{DD} to V_{SS}	+44 V
V_{DD} to GND	−0.3 V to +30 V
V_{SS} to GND	+0.3 V to −30 V
Analog, Digital Inputs ¹	$V_{SS} - 2\text{ V}$ to $V_{DD} + 2\text{ V}$ or 20 mA, whichever occurs first
Continuous Current, S or D	20 mA
Peak Current, S or D (Pulsed at 1 ms, 10% Duty Cycle Max)	40 mA
Operating Temperature Range	
Industrial (B Version)	−40°C to +85°C
Storage Temperature Range	−65°C to +125°C
Junction Temperature	150°C
θ_{JA} , Thermal Impedance	
PDIP Package	103°C/W
SOIC Package	74°C/W
SSOP Package	130°C/W
Lead Temperature, Soldering (10 sec)	260°C
Lead Temperature, Soldering Vapor Phase (60 sec)	215°C
Infrared (15 sec)	220°C
Lead Temperature, Soldering Vapor Phase (60 sec)	215°C
Infrared (15 sec)	220°C

¹ Overvoltage at IN, S, or D is clamped by internal diodes. Current should be limited to the maximum ratings given.

Stresses above those listed under Absolute Maximum Ratings may cause permanent damage to the device. This is a stress rating only; functional operation of the device at these or any other conditions above those indicated in the operational section of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

Table 4. Truth Table

Logic	Switch A	Switch B
0	Off	On
1	On	Off

ESD CAUTION

ESD (electrostatic discharge) sensitive device. Electrostatic charges as high as 4000 V readily accumulate on the human body and test equipment and can discharge without detection. Although this product features proprietary ESD protection circuitry, permanent damage may occur on devices subjected to high energy electrostatic discharges. Therefore, proper ESD precautions are recommended to avoid performance degradation or loss of functionality.



TERMINOLOGY

R_{ON}	t_{ON}
Ohmic resistance between D and S.	Delay between applying the digital control input and the output switching on.
ΔR_{ON}	t_{OFF}
R _{ON} variation due to a change in the analog input voltage with a constant load current.	Delay between applying the digital control input and the output switching off.
R_{ON} Match	t_{OPEN}
Difference between the R _{ON} of any two channels.	Break-before-make delay when switches are configured as a multiplexer.
I_S (OFF)	V_{INL}
Source leakage current with the switch off.	Maximum input voltage for Logic 0.
I_D (OFF)	V_{INH}
Drain leakage current with the switch off.	Minimum input voltage for Logic 1.
I_D, I_S (ON)	I_{INL} (I_{INH})
Channel leakage current with the switch on.	Input current of the digital input.
V_D (V_S)	Crosstalk
Analog voltage on Terminals D, S.	A measure of unwanted signal which is coupled through from one channel to another as a result of parasitic capacitance.
C_S (OFF)	Off Isolation
OFF switch source capacitance.	A measure of unwanted signal coupling through an OFF switch.
C_D (OFF)	Charge Injection
OFF switch drain capacitance.	A measure of the glitch impulse transferred from the digital input to the analog output during switching.
C_D, C_S (ON)	
ON switch capacitance.	

PIN CONFIGURATIONS AND FUNCTION DESCRIPTIONS

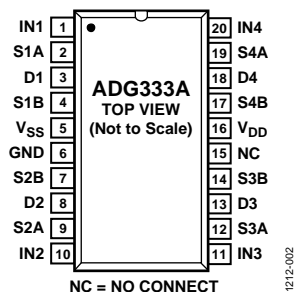


Figure 2. PDIP Pin Configuration

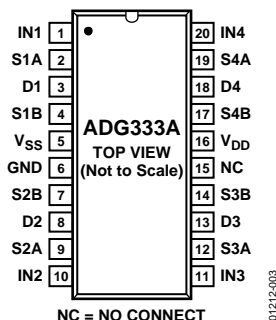


Figure 3. SOIC Pin Configuration

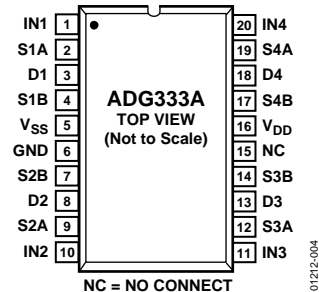


Figure 4. SSOP Pin Configuration

Table 5. Pin Function Descriptions

Pin No.	Mnemonic	Description
1, 10, 11, 20	IN1, IN2, IN3, IN4	Logic Control Input.
2, 4, 7, 9, 12, 14, 17, 19	S1A, S1B, S2B, S2A, S3A, S3B, S4B, S4A	Source Terminal. Can be an input or output.
3, 8, 13, 18	D1, D2, D3, D4	Drain Terminal. Can be an input or output.
5	V _{SS}	Most Negative Power Supply Potential in Dual Supplies. In single-supply applications, it can be connected to ground.
6	GND	Ground (0 V) Reference.
15	NC	No Connect.
16	V _{DD}	Most Positive Power Supply Potential.

TYPICAL PERFORMANCE CHARACTERISTICS

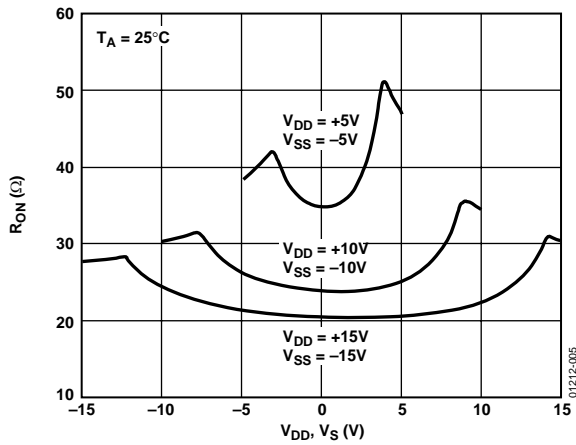


Figure 5. R_{ON} as a Function of V_D (V_S): Dual Supply

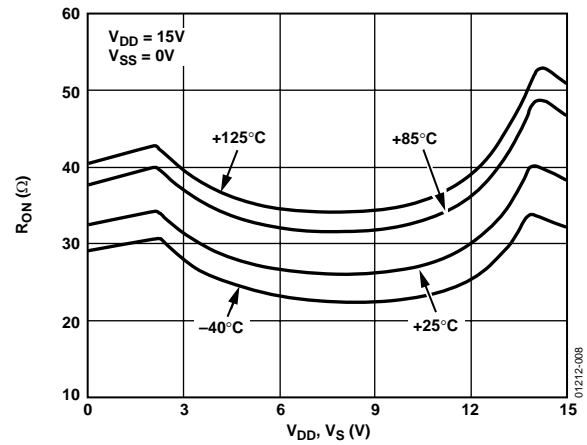


Figure 8. R_{ON} as a Function of V_D (V_S) for Different Temperatures: Single Supply

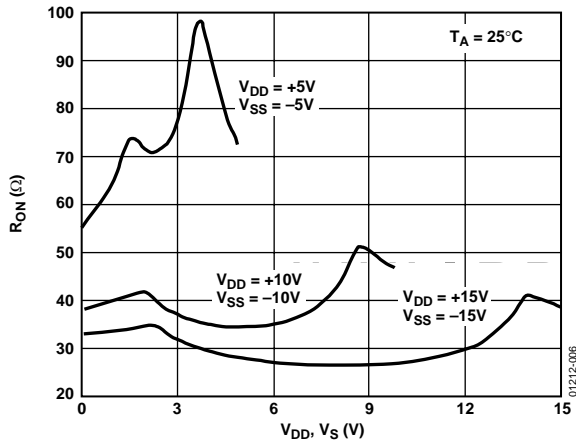


Figure 6. R_{ON} as a Function of V_D (V_S): Single Supply

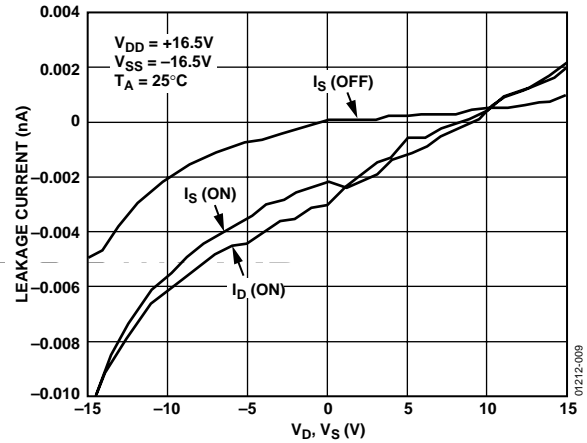


Figure 9. Leakage Currents as a Function of V_D (V_S): Dual Supply

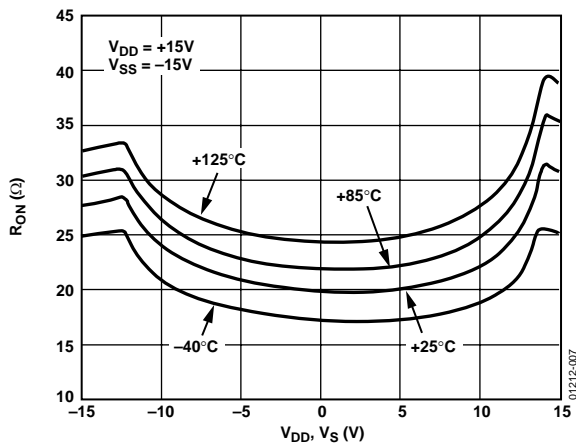


Figure 7. R_{ON} as a Function of V_D (V_S) for Different Temperatures: Dual Supply

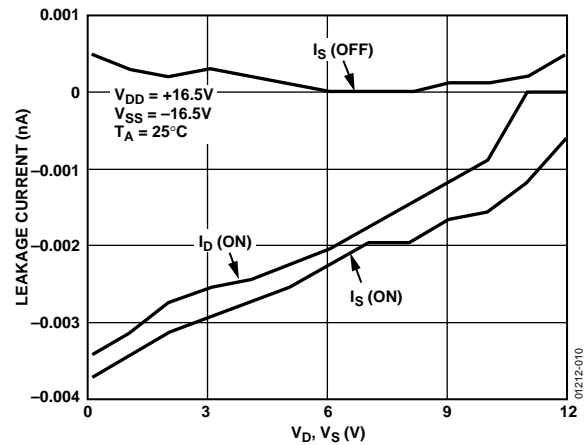


Figure 10. Leakage Currents as a Function of V_D (V_S): Single Supply

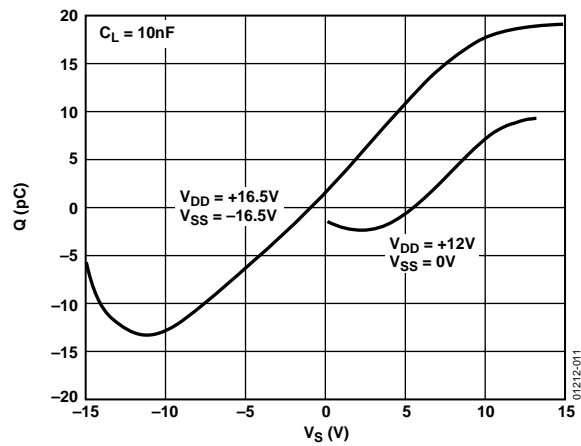


Figure 11. Charge Injection as a Function of V_S

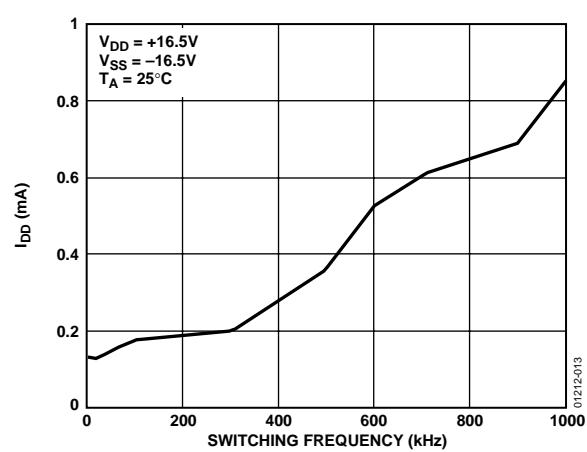


Figure 13. I_{DD} as a Function of Switching Frequency

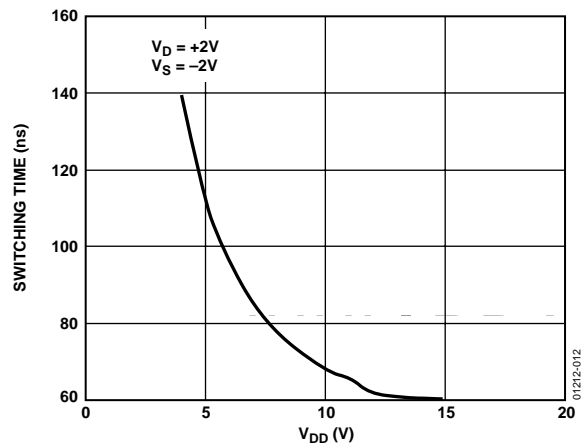


Figure 12. Switching Time as a Function of V_D

TEST CIRCUITS

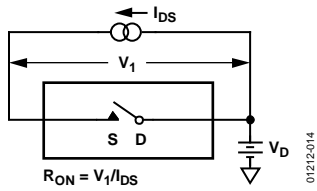


Figure 14. On Resistance

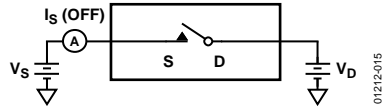


Figure 15. Off Leakage

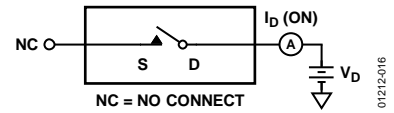


Figure 16. On Leakage

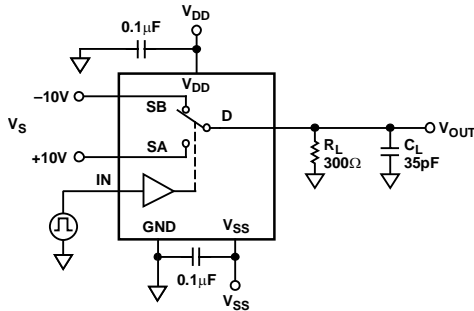


Figure 17. Switching Times

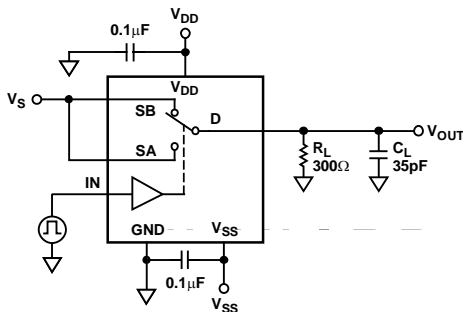
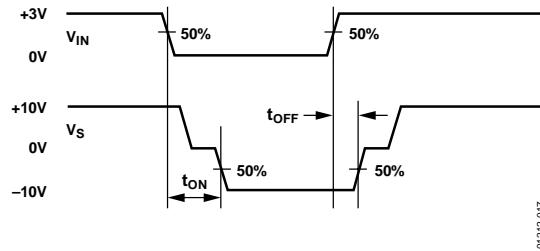


Figure 18. Break-Before-Make Delay, t_{OPEN}

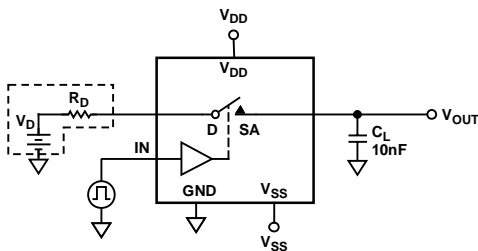
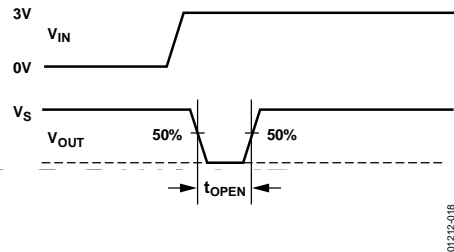


Figure 19. Charge Injection

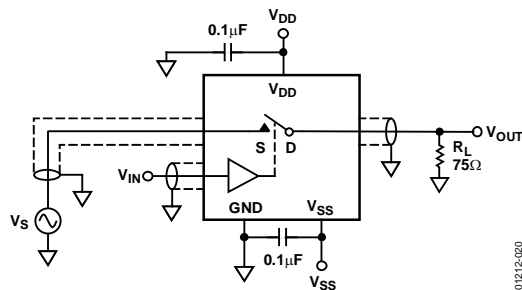
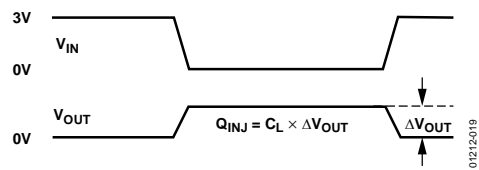


Figure 20. Off Isolation

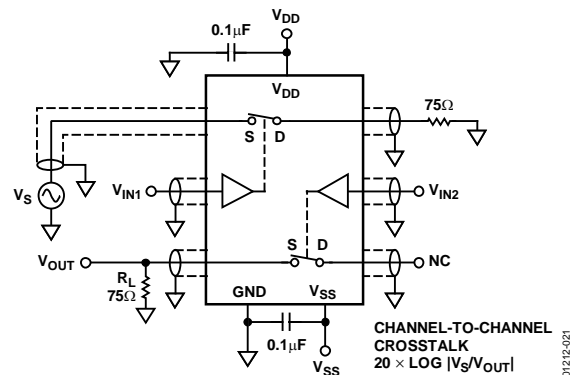


Figure 21. Channel-to-Channel Crosstalk

APPLICATION INFORMATION

ADG333A SUPPLY VOLTAGES

The ADG333A can operate from a dual or signal supply. V_{SS} should be connected to GND when operating with a single supply. When using a dual supply, the ADG333A can also operate with unbalanced supplies; for example $V_{DD} = 20\text{ V}$ and $V_{SS} = -5\text{ V}$. The only restrictions are that V_{DD} to GND must not exceed 30 V, V_{SS} to GND must not drop below -30 V , and V_{DD} to V_{SS} must not exceed +44 V. It is important to remember that the ADG333A supply voltage directly affects the input signal range, the switch on resistance and the switching times of the part. The effects of the power supplies on these characteristics can be clearly seen from the Typical Performance Characteristics curves.

POWER SUPPLY SEQUENCING

When using CMOS devices, care must be taken to ensure correct power-supply sequencing. Incorrect power-supply sequencing can result in the device being subjected to stresses beyond those listed in the Absolute Maximum Ratings. This is also true for the ADG333A. Always turn on V_{DD} first, followed by V_{SS} and the logic signals. An external signal within the maximum specified ratings can then be safely presented to the source or drain of the switch

